



STGW38IH130D STGWT38IH130D

33 A - 1300 V - very fast IGBT

Features

- Low saturation voltage
- High current capability
- Low switching loss
- Low static and peak forward voltage drop free-wheeling diode

Applications

- Induction cooking, microwave ovens
- Soft-switching applications

Description

This device is a very fast IGBT developed using advanced PowerMESH™ technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. This device is well-suited for resonant or soft-switching applications.

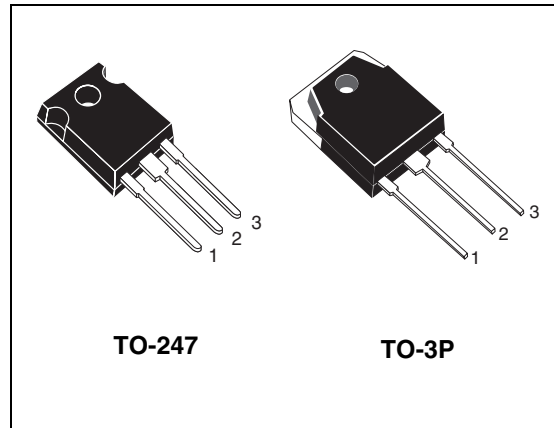


Figure 1. Internal schematic diagram

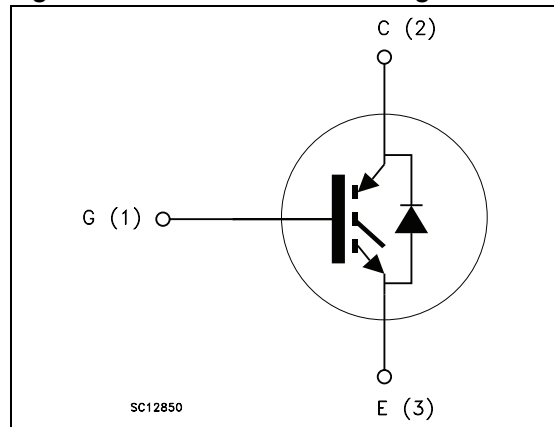


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGWT38IH130D	GW38IH130D	TO-247 long leads	Tube
STGWS38IH130D		TO-247	
STGWT38IH130D		TO-3P	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-3P, TO-247 long leads	TO-247	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	1300		V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	63	55	A
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	33	25	A
I _{CL} ⁽²⁾	Turn-off latching current	40		A
I _{CP} ⁽³⁾	Pulsed collector current	125		A
V _{GE}	Gate-emitter voltage	±25		V
P _{TOT}	Total dissipation at T _C = 25 °C	250	180	W
I _F	Diode RMS forward current at T _C = 25 °C	30		A
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal	100		A
T _j	Operating junction temperature	-55 to 150		°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(\max)} - T_C}{R_{thj-c} \times V_{CE(sat)(\max)}(T_{j(\max)}, I_C(T_C))}$$

2. V_{clamp} = 960 V, T_j = 150 °C, R_G = 10 Ω, V_{GE} = 15 V

3. Pulse width limited by maximum permissible junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-3P, TO-247 long leads	TO-247	
R _{thj-case}	Thermal resistance junction-case IGBT	0.5	0.7	°C/W
R _{thj-case}	Thermal resistance junction-case diode	2	2.1	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	50		°C/W

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	1300			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$, $T_J = 125\text{ °C}$		2.1 2.0	2.8	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	3.75		5.75	V
I_{CES}	Collector-cut-off current ($V_{GE} = 0$)	$V_{CE} = 1300\text{ V}$ $V_{CE} = 1300\text{ V}$, $T_J = 125\text{ °C}$			1 10	mA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 25\text{ V}$, $I_C = 20\text{ A}$		20		S
V_F	Diode forward voltage	$I_F = 20\text{ A}$ $I_F = 20\text{ A}$, $T_J = 125\text{ °C}$		1.3	1.9 1.7	V V

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	2900	-	pF
C_{oes}	Output capacitance			155		pF
C_{res}	Reverse transfer capacitance			30		pF
Q_g	Total gate charge	$V_{CE} = 960\text{ V}$, $I_C = 20\text{ A}$, $V_{GE} = 15\text{ V}$	-	127	-	nC
Q_{ge}	Gate-emitter charge			18		nC
Q_{gc}	Gate-collector charge			50		nC

Table 6. Inductive load switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, <i>(see Figure 16)</i>	-	102	-	ns
$t_{d(off)}$	Turn-off delay time			284		ns
t_f	Current fall time			180		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ °C}$ <i>(see Figure 16)</i>	-	200	-	ns
$t_{d(off)}$	Turn-off delay time			424		ns
t_f	Current fall time			316		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{\text{off}}^{(1)}$	Turn-off switching losses	$V_{\text{CC}} = 960 \text{ V}$, $I_{\text{C}} = 20 \text{ A}$ $R_{\text{G}} = 10 \text{ } \Omega$, $V_{\text{GE}} = 15 \text{ V}$, (see Figure 16)	-	3.4	-	mJ
$E_{\text{off}}^{(1)}$	Turn-off switching losses	$V_{\text{CC}} = 960 \text{ V}$, $I_{\text{C}} = 20 \text{ A}$ $R_{\text{G}} = 10 \text{ } \Omega$, $V_{\text{GE}} = 15 \text{ V}$, $T_{\text{J}} = 125 \text{ } ^\circ\text{C}$ (see Figure 16)	-	6.4	-	mJ

1. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

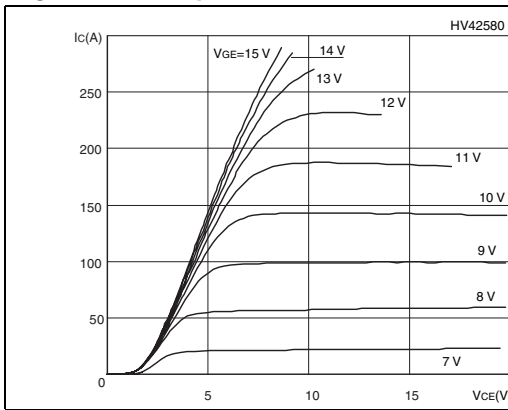


Figure 3. Transfer characteristics

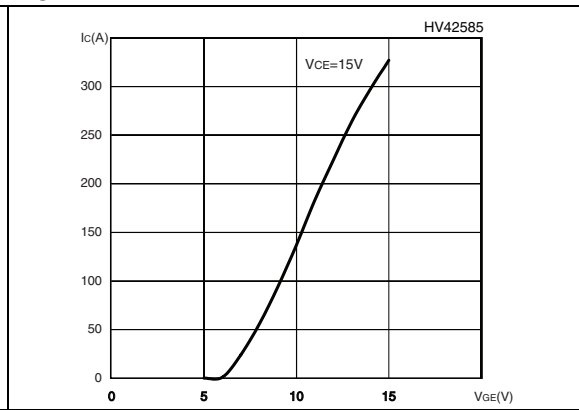


Figure 4. Transconductance

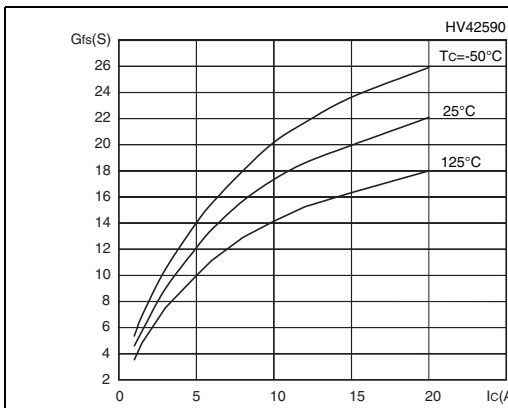


Figure 5. Collector-emitter on voltage vs. temperature

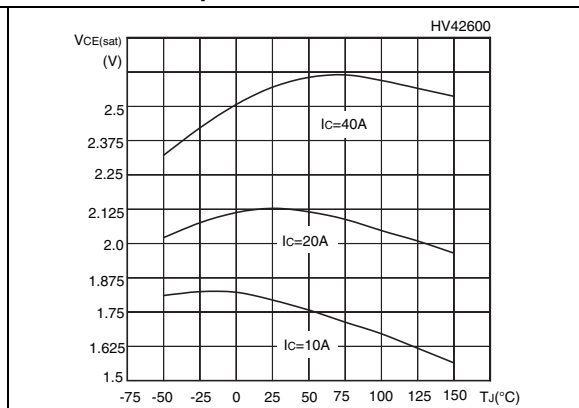


Figure 6. Normalized breakdown voltage vs. temperature

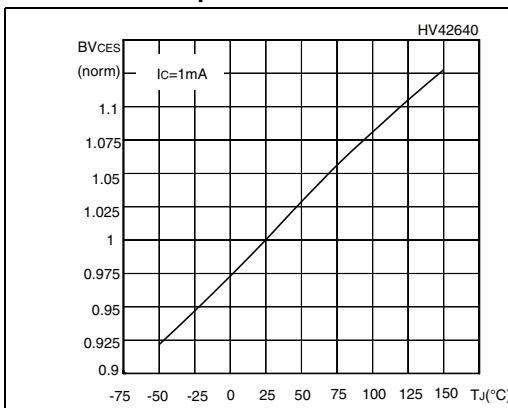


Figure 7. Gate-charge vs. gate-emitter

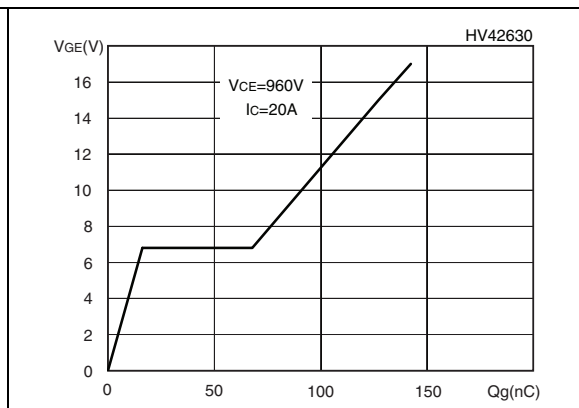


Figure 8. Normalized gate threshold voltage vs. temperature

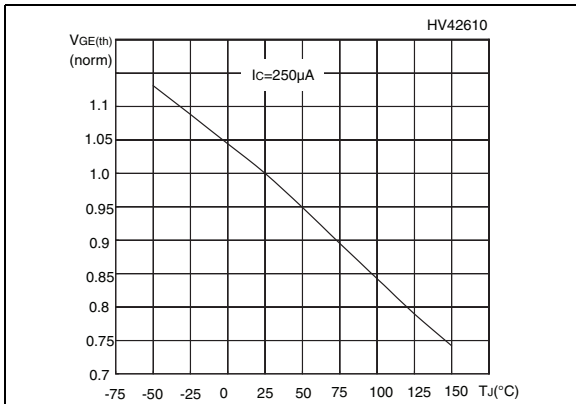


Figure 9. Collector-emitter on voltage vs. collector current

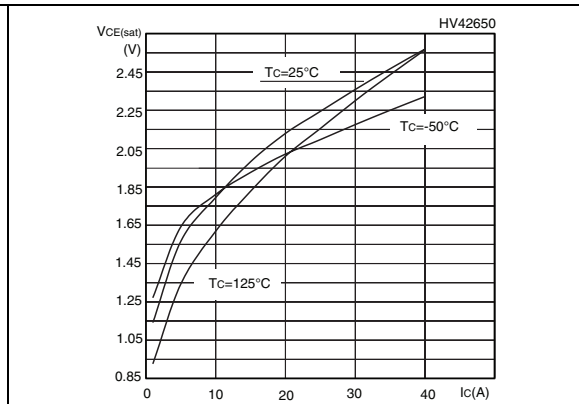


Figure 10. Switching losses vs. temperature

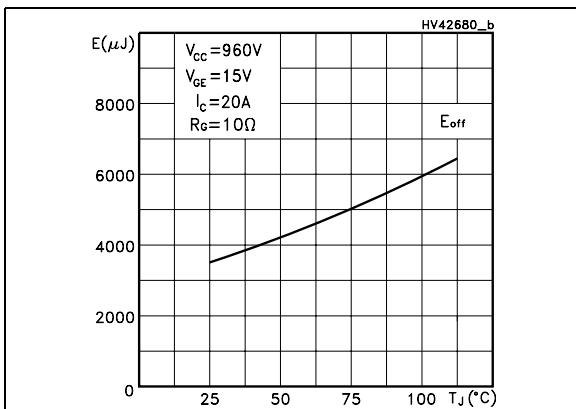


Figure 11. Switching losses vs. gate resistance

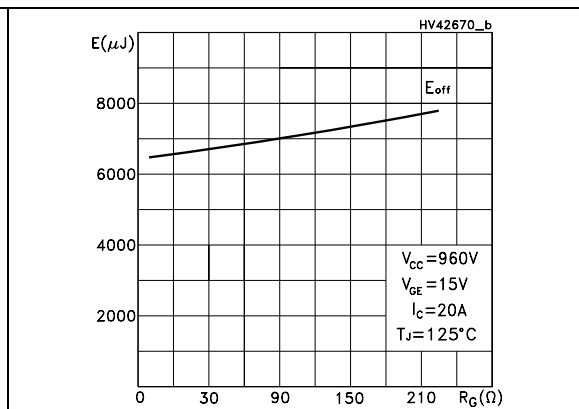


Figure 12. Switching losses vs. collector current

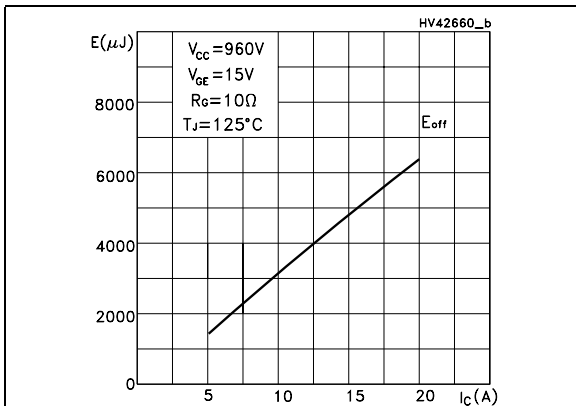


Figure 13. RBSOA

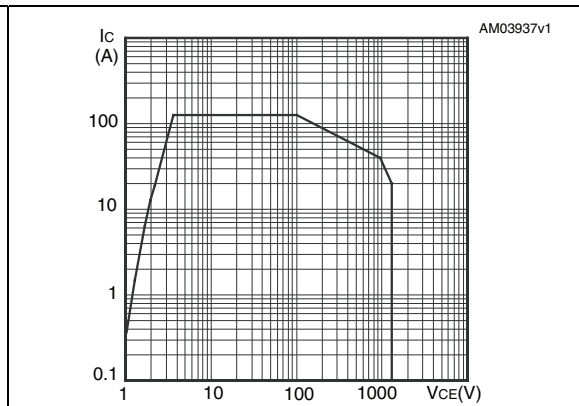


Figure 14. Emitter-collector diode characteristics

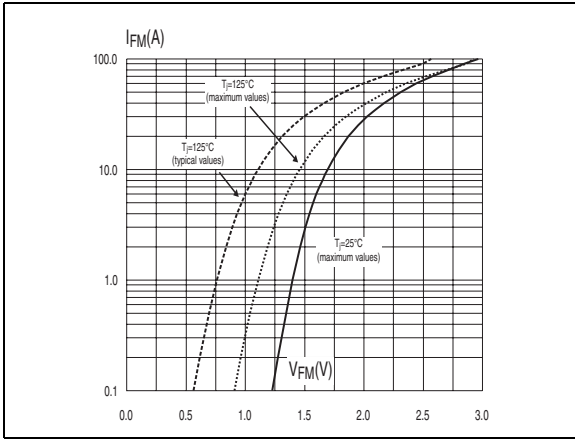
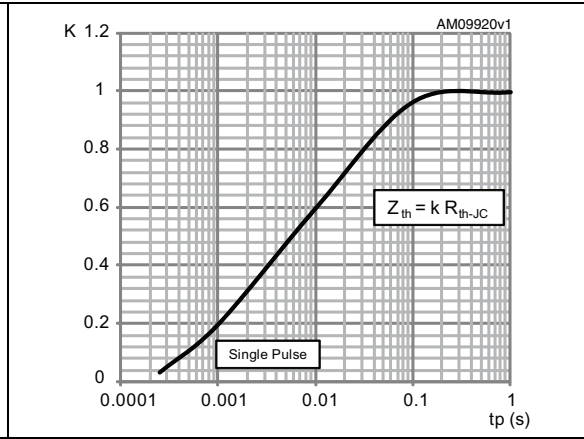


Figure 15. Thermal impedance



3 Test circuits

Figure 16. Test circuit for inductive load switching

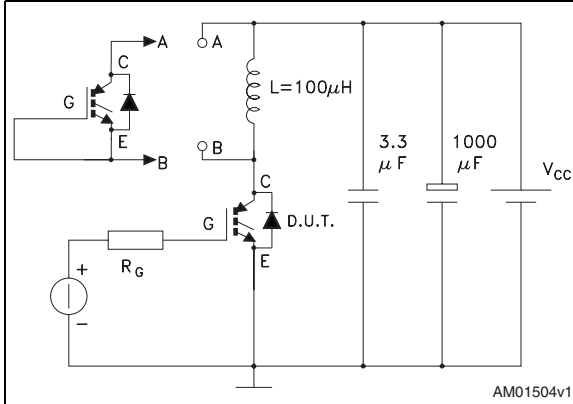


Figure 17. Gate charge test circuit

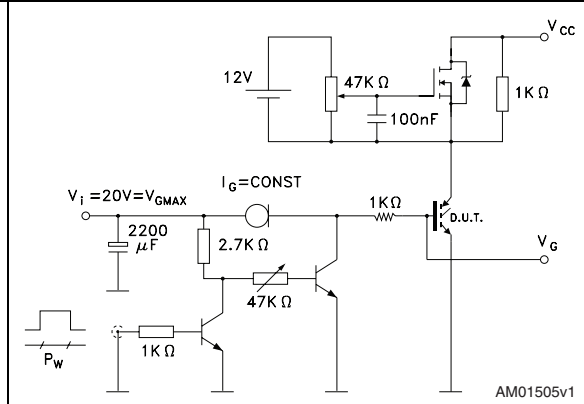
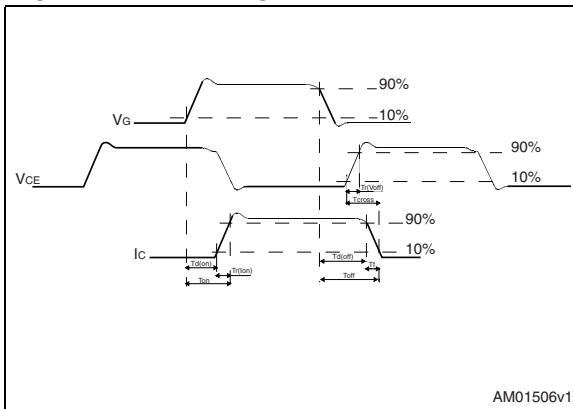


Figure 18. Switching waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	

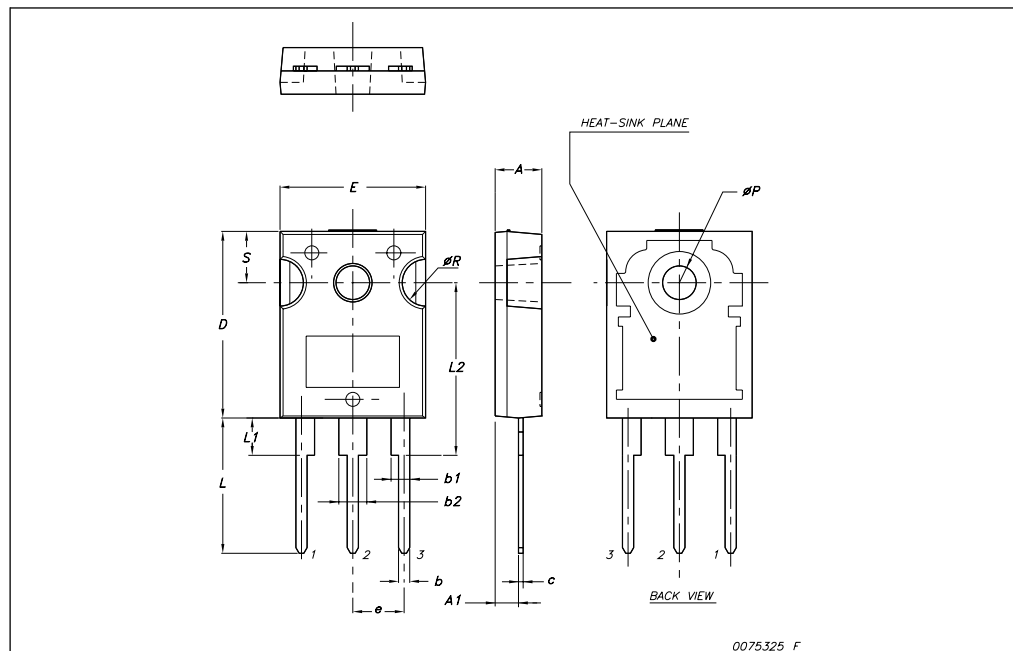


Table 8. TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90		5.15
D	1.85		2.10
E	0.55		0.67
F	1.07		1.32
F1	1.90		2.38
F2	2.87		3.38
G	10.90 BSC		
H	15.77		16.02
L	20.82		21.07
L1	4.16		4.47
L2	5.49		5.74
L3	20.05		20.30
L4	3.68		3.93
L5	6.04		6.29
M	2.27		2.52
V		10°	
V1		3°	
V3		20°	
Dia.	3.55		3.66

Figure 19. TO-247 long leads drawing

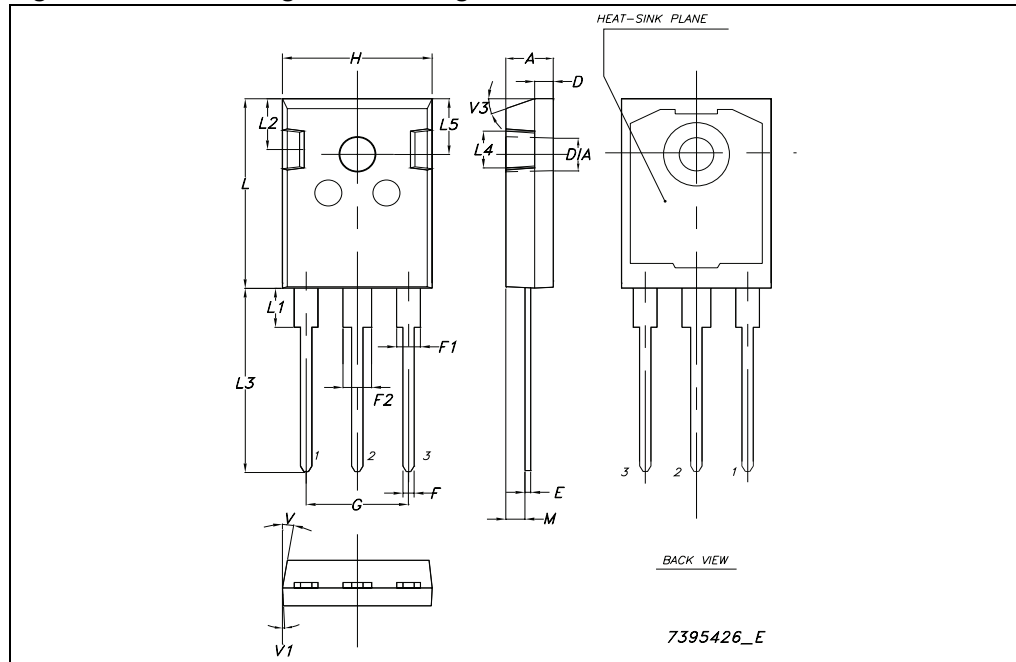
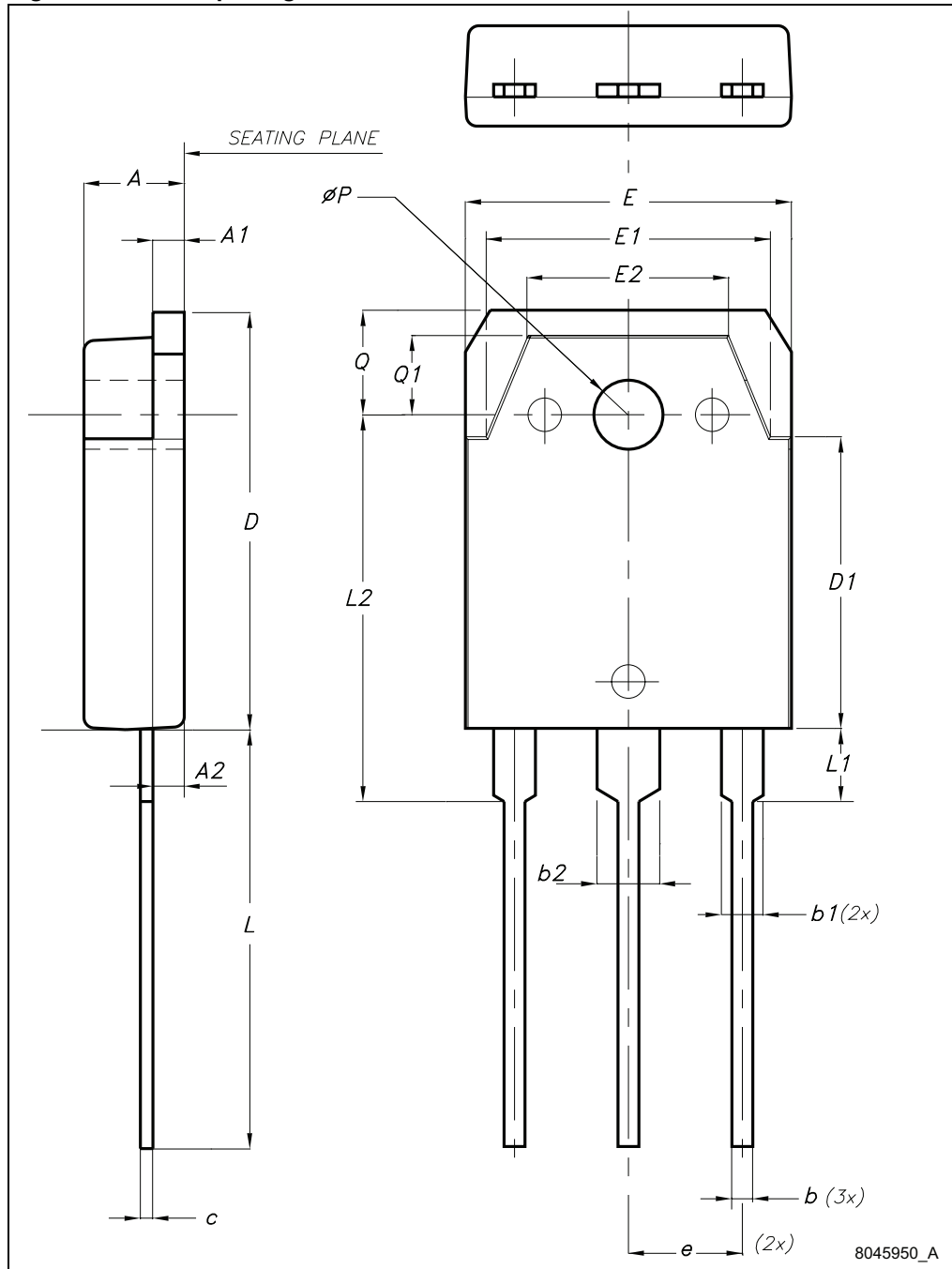


Table 9. TO-3P mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.60		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
øP	3.10		3.30
Q		5	
Q1		3.80	

Figure 20. TO-3P package dimensions



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
11-May-2009	1	Initial release
16-Jul-2009	2	Document status promoted from preliminary data to datasheet
05-Jul-2011	3	Added: Figure 15 on page 8 and new package mechanical data Table 9 on page 14 , Figure 20 on page 15

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